

CLAIM AMENDMENTS

1. (Currently Amended) A semiconductor integrated circuit device comprising:
a resonant circuit ~~which makes resonance~~ resonating at an arbitrary frequency;
a transmission line for transmitting a high-frequency signal having said frequency,
~~one of two wherein a first end portions~~ of said transmission line being connected to said
resonant circuit;

an active element having a first electrode connected to ~~the other~~ a second end
~~portion~~ of said transmission line, a second electrode which is grounded through a reactance
element, and a third electrode;

an output-matching circuit including a diode section for regulating an oscillation
power and a high-frequency signal output terminal, ~~one of two wherein a first end portions~~ of
said diode section being is connected to said third electrode of said active element, and said
high-frequency signal output terminal being is connected to ~~the other~~ a second end portion of
said diode section; and

a substrate having a main surface on which said resonant circuit, said transmission
line, said active element and said output-matching circuit are arranged.

2. (Currently Amended) The semiconductor integrated circuit device according to
claim 1, wherein said diode section includes a plurality of diodes ~~arranged in~~ having an
inverse parallel ~~manner~~ arrangement.

3. (Original) The semiconductor integrated circuit device according to claim 1,
wherein said diode section includes a plurality of diodes arranged in series.

4. (Original) The semiconductor integrated circuit device according to claim 1,
further comprising a bias circuit for applying a DC bias to said diode section.

5. (Currently Amended) A semiconductor integrated circuit device comprising:
a resonant circuit ~~which makes resonance~~ resonating at an arbitrary frequency;
a transmission line for transmitting a high-frequency signal having said frequency,
~~one of two wherein a first end portions~~ of said transmission line being connected to said
resonant circuit;

an oscillation power regulating circuit including a diode section for regulating an
oscillation power, ~~one end portion of wherein~~ said oscillation power regulating circuit being
is connected to ~~the other~~ a second end portion of said transmission line;

an active element having a first electrode connected to the ~~other~~ second end ~~portion~~ of said transmission line, a second electrode which is grounded through a reactance element, and a third electrode;

an output-matching circuit including a high-frequency signal output terminal, wherein said output-matching circuit ~~being~~ is connected to said third electrode of said active element; and

a substrate having a main surface on which said resonant circuit, said transmission line, said oscillation power regulating circuit, said active element and said output-matching circuit are arranged.

6. (Currently Amended) The semiconductor integrated circuit device according to claim 5, wherein said diode section includes a plurality of diodes ~~arranged in~~ having an inverse parallel ~~manner~~ arrangement.

7. (Original) The semiconductor integrated circuit device according to claim 5, wherein said diode section includes a plurality of diodes arranged in series.

8. (Original) The semiconductor integrated circuit device according to claim 5, further comprising a bias circuit for applying a DC bias to said diode section.